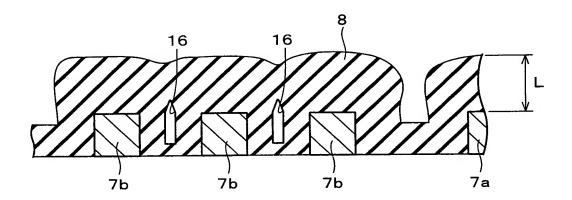
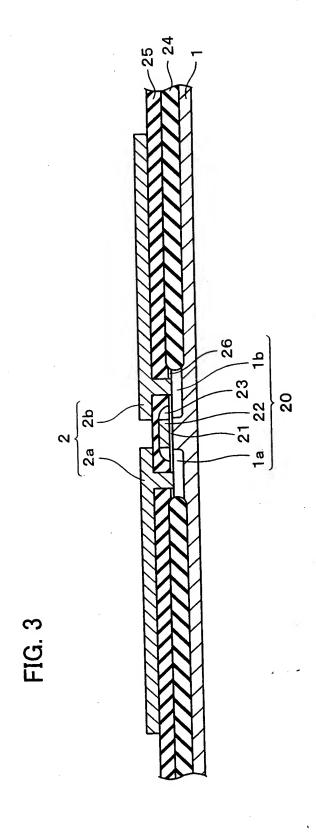


FIG. 2





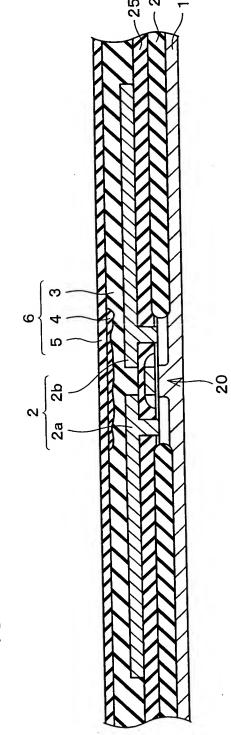
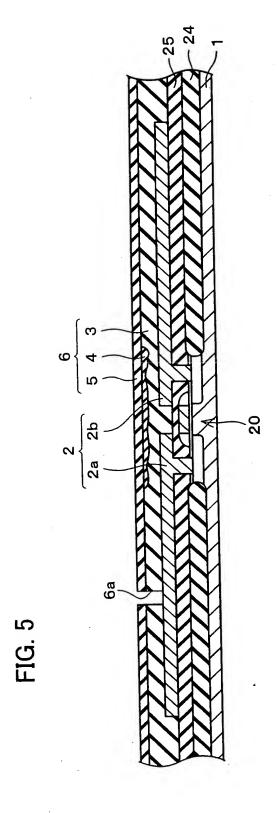


FIG. 4



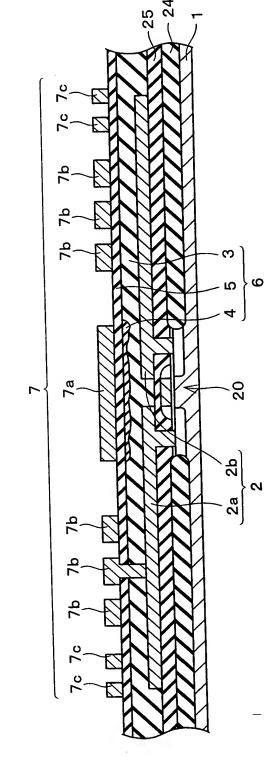


FIG. 6

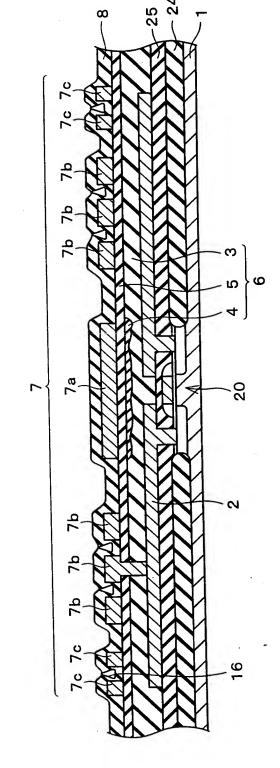


FIG. 7

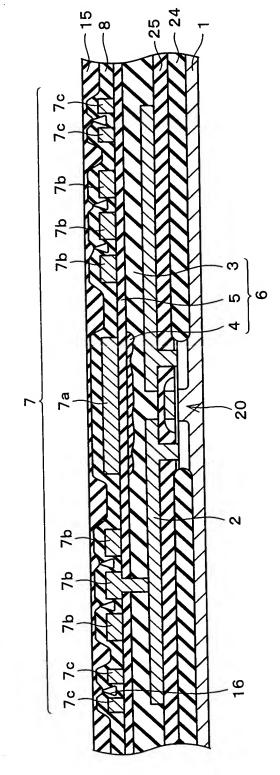
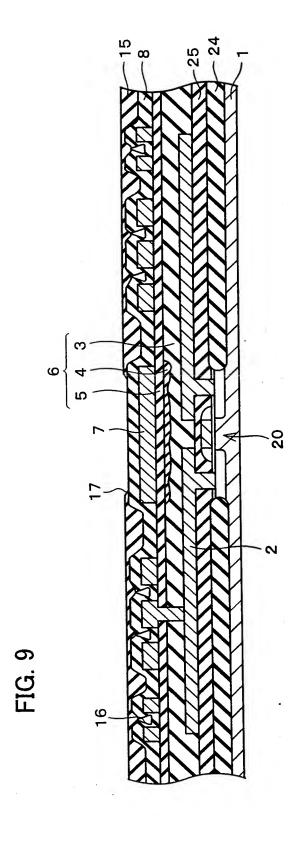
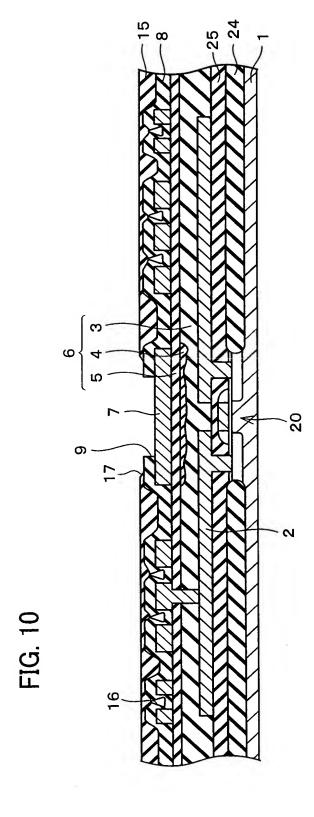


FIG. 8





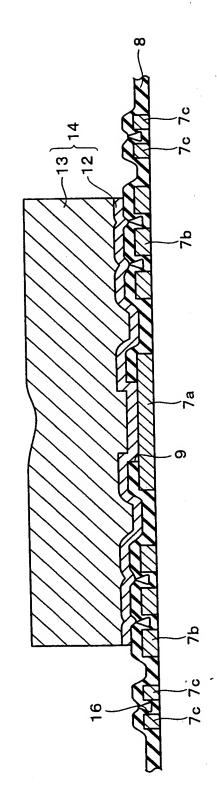


FIG. 1

FIG. 12

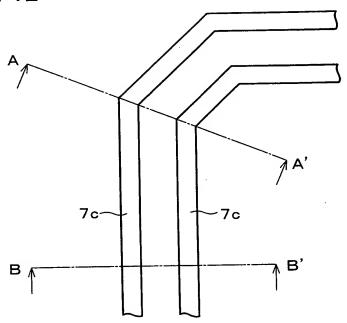


FIG. 13 (a)

28

8

7c

7c

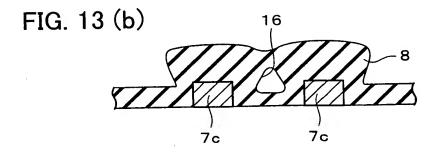
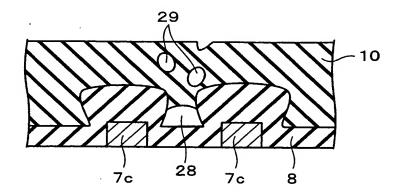


FIG. 14



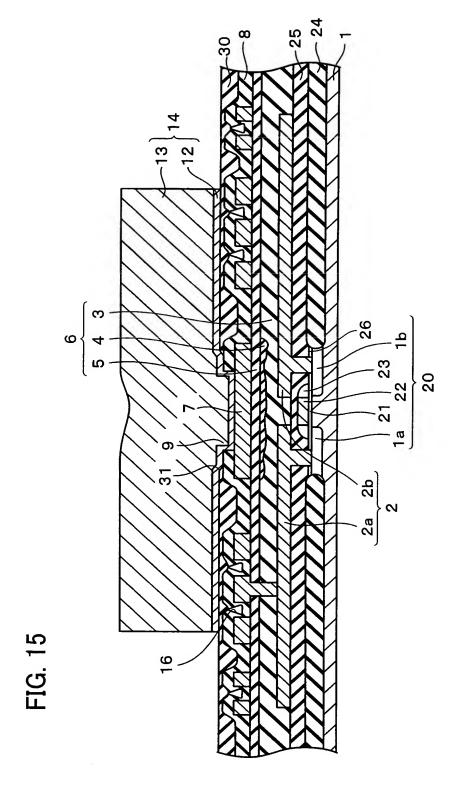


FIG. 16 (a)

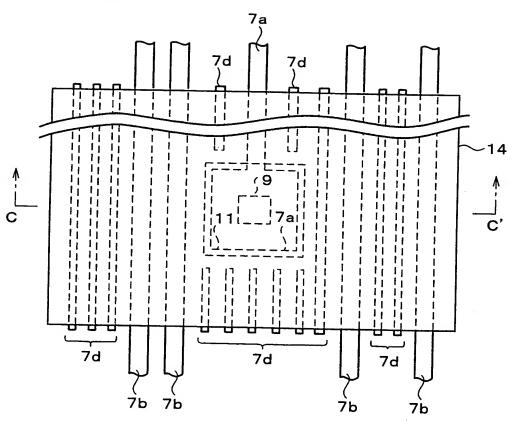
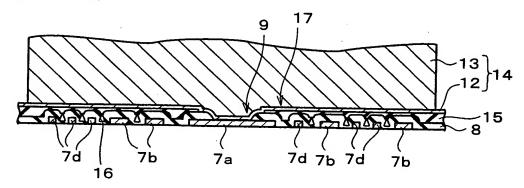
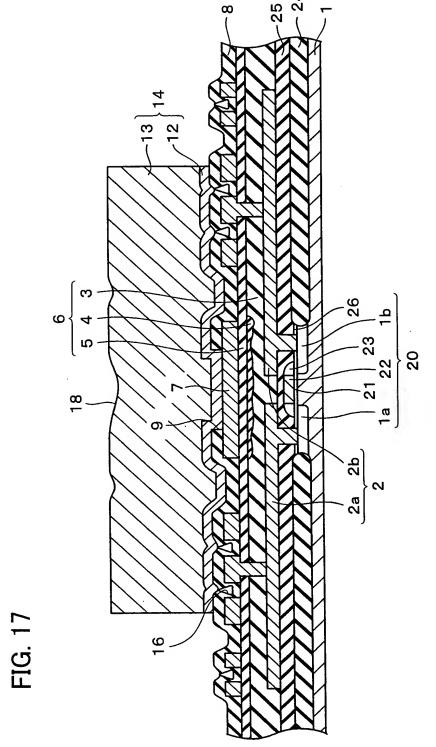


FIG. 16 (b)





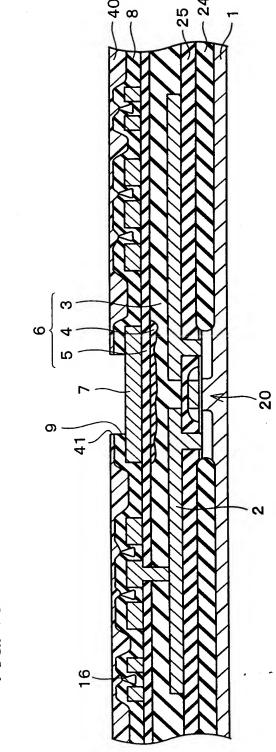


FIG. 18

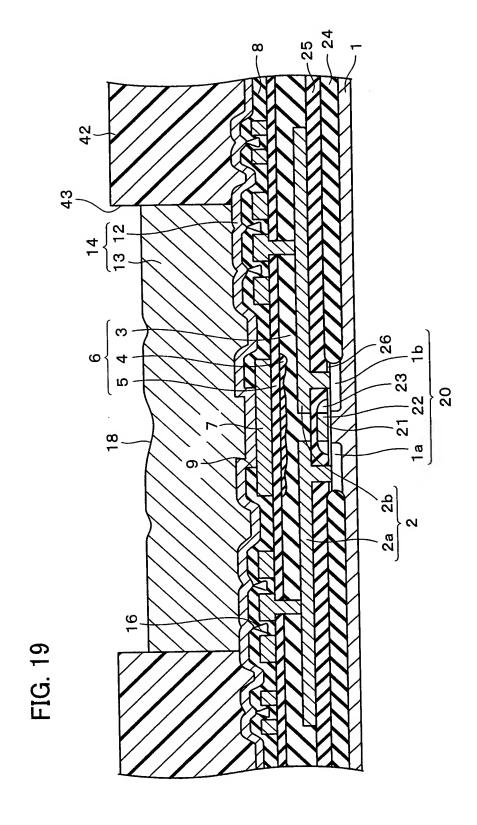


FIG. 20

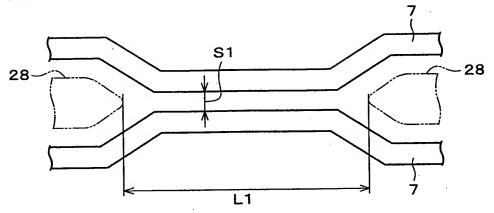


FIG. 21

THICKNESS OF PROTECTIVE LAYER: $t=1.2 \mu$ m

S1 L1	400	900	1400	1900
0.8	0	Δ	×	×
1.2	0	Δ	Δ	×
1.5	0	Δ	Δ	×
1.8	0	0	0	0

	SCATTERING OF RESIST MATERIAL	SWELLING OF PHOTORESIST LAYER
0	ABSENT	ABSENT
Δ	ABSENT	PRESENT
×	PRESENT	PRESENT

FIG. 22

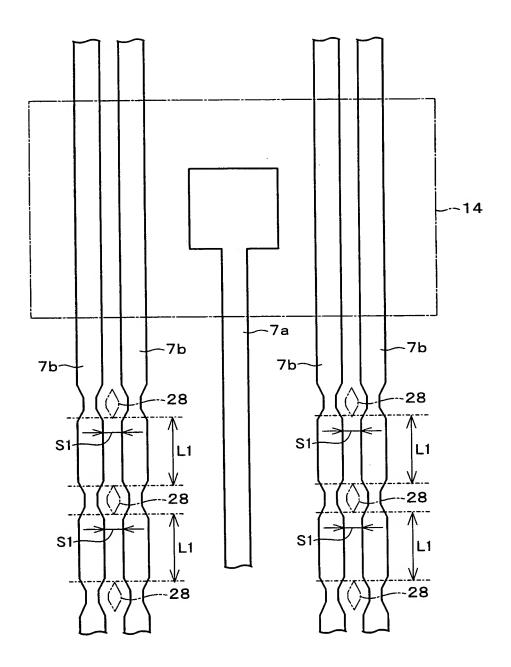


FIG. 23

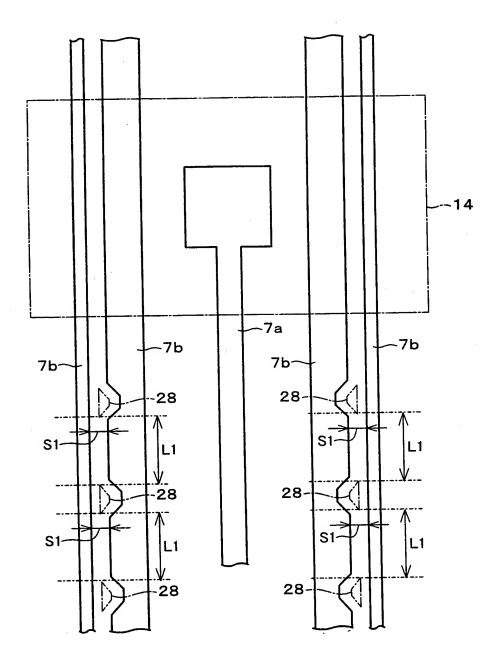


FIG. 24

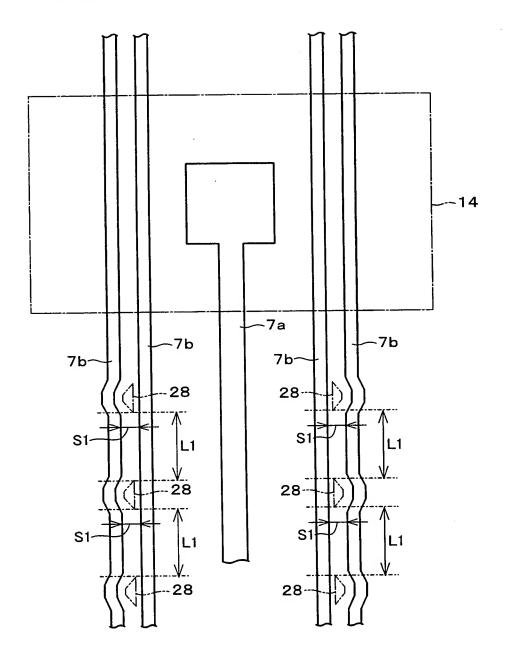


FIG. 25

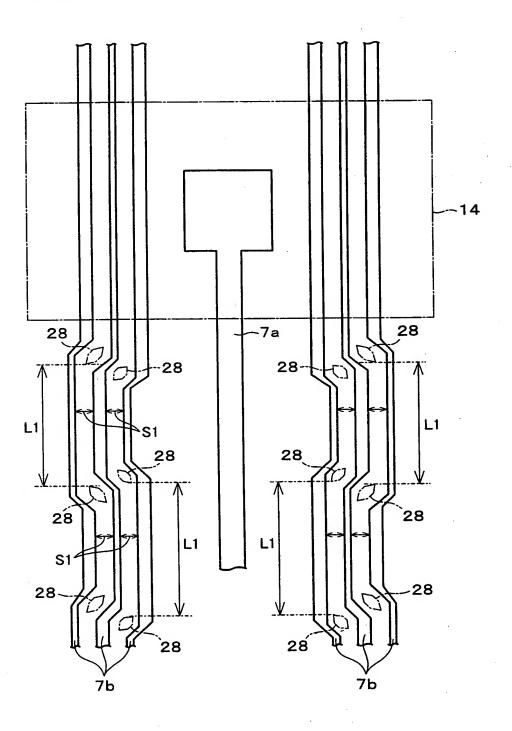


FIG. 26

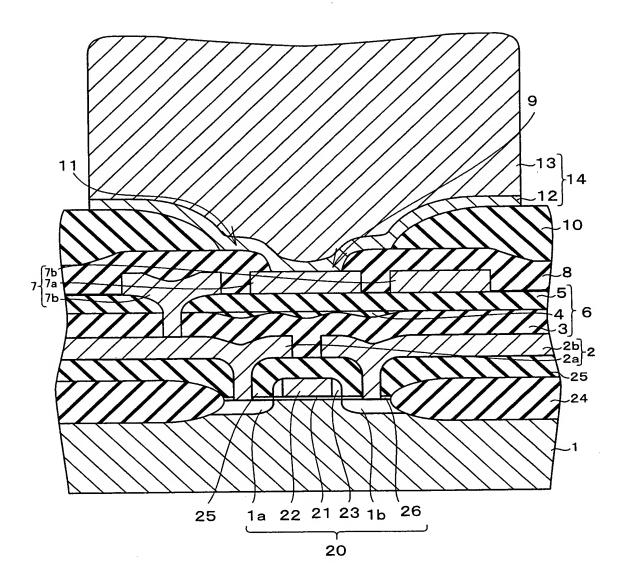


FIG. 27

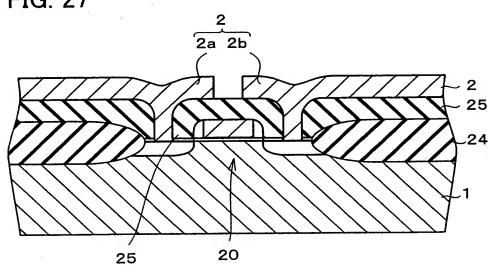


FIG. 28

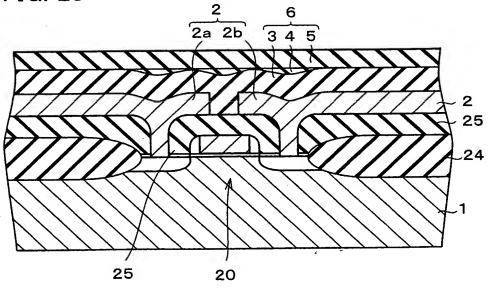


FIG. 29

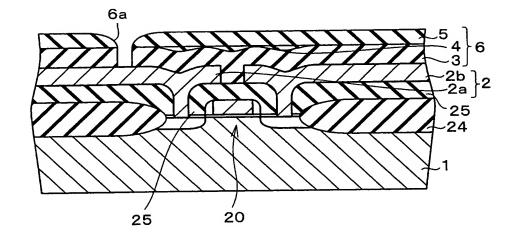


FIG. 30

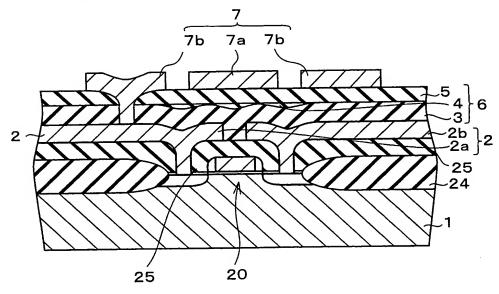


FIG. 31

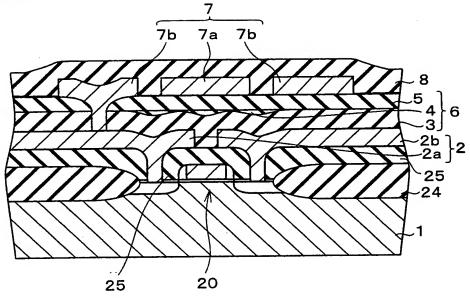


FIG. 32

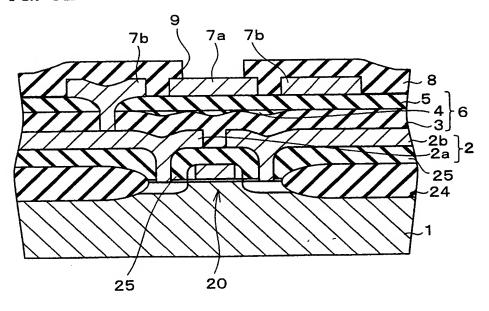


FIG. 33

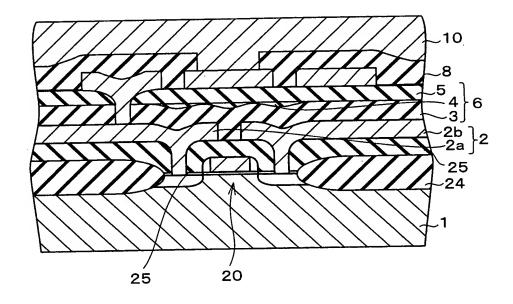


FIG. 34

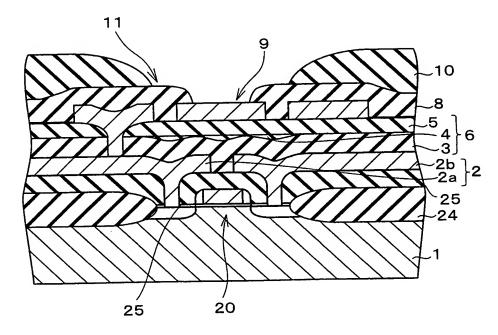


FIG. 35 (a)

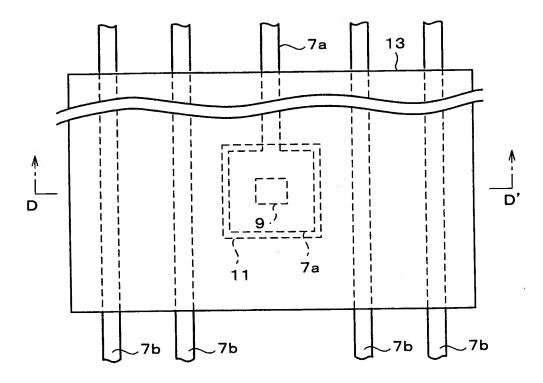


FIG. 35 (b)

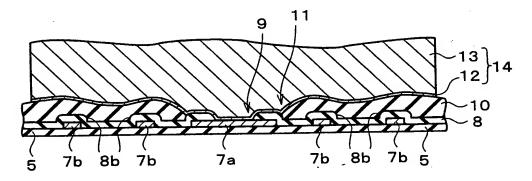


FIG. 36

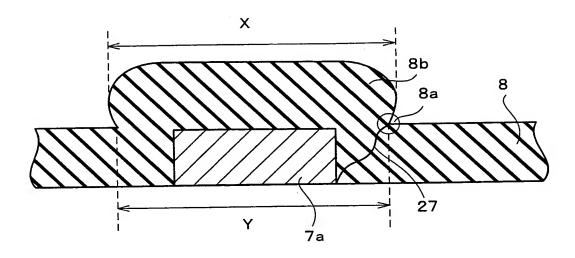


FIG. 37

